

2STW4466

High power NPN epitaxial planar bipolar transistor

Features

- High breakdown voltage V_{CEO} = 80 V
- Complementary to 2STW1693
- Typical f_t = 20 MHz
- Fully characterized at 125 °C

Applications

Audio power amplifier

Description

The device is a NPN transistor manufactured in low voltage planar technology using base island layout. The resulting transistor shows good gain linearity coupled with low $V_{CE(sat)}$ behaviour. Recommended for 40 W to 70 W high fidelity audio frequency amplifier output stage.

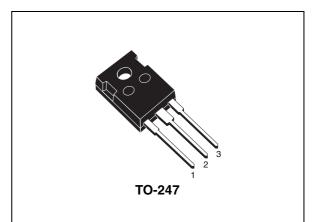


Figure 1. Internal schematic diagram

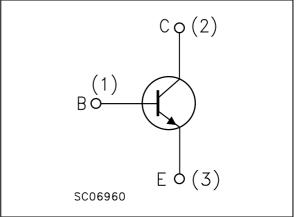


Table	1.	Device	summary
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Order code	Marking	Package	Packaging
2STW4466	2STW4466	TO-247	Tube

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Electrical ratings 1

Table 2.	Absolute	maxir
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Table 2.	Absolute maximum rating		
Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage ($I_E = 0$)	100	V
V _{CEO}	Collector-emitter voltage ($I_B = 0$)	80	V
V _{EBO}	Emitter-base voltage ($I_C = 0$)	6	V
۱ _C	Collector current	6	А
I _{CM}	Collector peak current (t _P < 5 ms)	12	А
P _{TOT}	Total dissipation at $T_c = 25 \text{ °C}$	60	W
T _{stg}	Storage temperature	-65 to 150	°C
Т _Ј	Max. operating junction temperature	150	°C

Thermal data Table 3.

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	2.08	°C/W



2 Electrical characteristics

 $(T_{case} = 25^{\circ}C; unless otherwise specified)$

Symbol	Parameter	Test co	nditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E = 0)	V _{CB} = 100 V				0.1	μA
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 6 V				0.1	μA
V _{(BR)EBO}	Emitter-base breakdown voltage (I _C = 0)	I _E = 1 mA		6			V
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = 100 μA		100			v
V _{(BR)CEO}	Collector-emitter breakdown voltage (I _B = 0)	l _C = 50 mA		80			v
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	I _C = 2 I _C = 6 A	I _B = 200 mA I _B = 600 mA			0.6 1.5	V V
$V_{BE}^{(1)}$	Base-emitter voltage	$V_{CE} = 4 V$	I _C = 6 A			1.5	V
h _{FE}	DC current gain	I _C = 2 A	$V_{CE} = 4 V$	50		120	
f _T	Transition frequency	I _C = 0.5 A	V _{CE} = 12 V		20		MHz
C _{CBO}	Collector-base capacitance $(I_E = 0)$	V _{CB} = 10 V	f = 1 MHz		50		pF
	Resistive load						
t _{on}	Turn-on time	I _C = 3 A	$V_{CC} = 30 V$		0.15		ns
t _{stg}	Storage time	$I_{B1} = -I_{B2} = 0.3$	A		1.5		ns
t _f	Fall time				0.1		ns

Table 4. Electrical characteristics

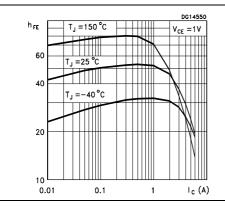
Pulsed duration = 300 $\mu s,$ duty cycle $\leq 1.5\%$

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2.1 Electrical characteristics (curves)

Figure 2. DC current gain

Figure 3. DC current gain



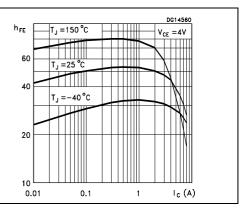
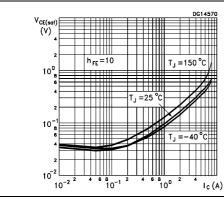


Figure 4. Collector-emitter saturation Figure 5. voltage



. Base-emitter saturation voltage

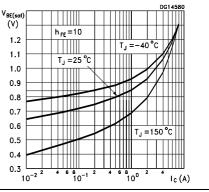
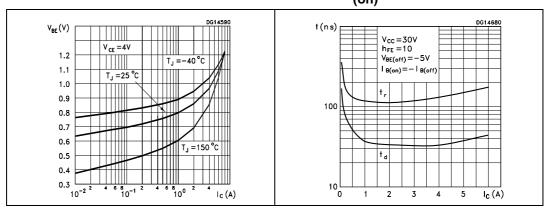


Figure 6. Base emitter voltage

Figure 7. Resistive load switching time (on)





Emitter-base and collector-

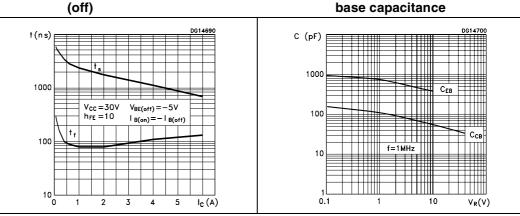


Figure 8. Resistive load switching time Figure 9. (off)

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3 Package mechanical data

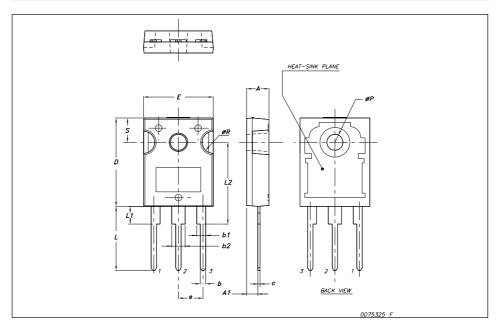
In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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Dim.	mm.			
	Min.	Тур	Max.	
A	4.85		5.15	
A1	2.20		2.60	
b	1.0		1.40	
b1	2.0		2.40	
b2	3.0		3.40	
с	0.40		0.80	
D	19.85		20.15	
E	15.45		15.75	
е		5.45		
L	14.20		14.80	
L1	3.70		4.30	
L2		18.50		
øP	3.55		3.65	
øR	4.50		5.50	
S		5.50		

TO-247 Mechanical data



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4 Revision history

Table 5.Document revision history

Date	Revision	Changes	
11-Oct-2007	1	First release	
25-Sep-2008	2	Content reworked to improve readability, no technical changes.	

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